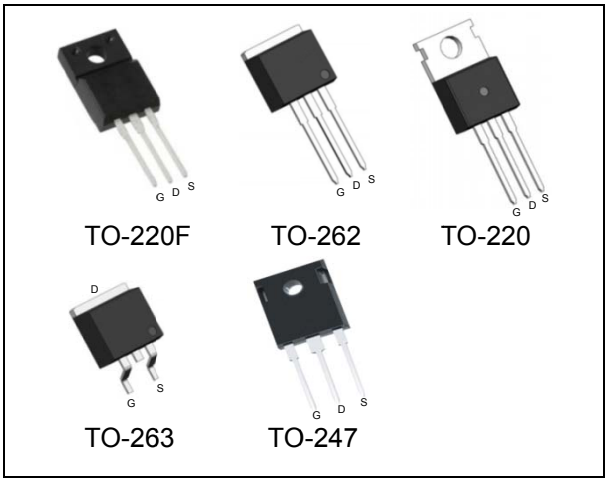
650V 0.165Ω Super Junction Power MOSFET

Description

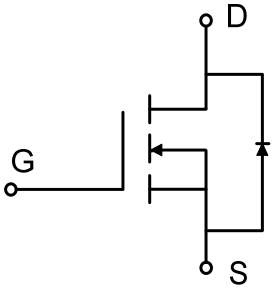
WMOS™ EM is Wayon's 3rd generation super junction MOSFET family that is utilizing charge balance technology for extremely low on-resistance and low gate charge performance. WMOS™ EM is suitable for applications which require superior power density and outstanding efficiency.



Features

- V_{DS} =700V @ $T_{j,max}$
- Typ. $R_{DS(on)}$ =0.165Ω
- 100% UIS tested
- Pb-free plating, Halogen free

RoHS compliant



Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server

Absolute Maximum Ratings

Parameter	Symbol	WMK/WMM/WMN/WMJ	WML	Unit
Drain-source voltage	V_{DSS}	650		V
Continuous drain current[1] (T_C = 25°C)	I_D	22		A
(T_C = 100°C)		13		A
Pulsed drain current[2]	I_{DM}	80		A
Gate-source voltage	V_{GS}	±30		V
Avalanche energy, single pulse[3]	E_{AS}	418		mJ
Avalanche energy, repetitive[2]	E_{AR}	0.6		mJ
Avalanche current, repetitive[2]	I_{AR}	3.8		A
Power dissipation (T_C = 25°C)	P_D	147	34	W
- Derate above 25°C		1.18	0.27	W/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to +150		°C
Continuous diode forward current[1]	I_S	22		A
Diode pulse current[2]	$I_{S,pulse}$	80		A

Thermal Characteristics

Parameter	Symbol	WMK/WMM/WMN/WMJ	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.85	3.7	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	°C/W

Electrical Characteristics T_c = 25°C, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=0.25 mA	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.25mA	2	3	4	V
Drain cut-off current	I_{DSS}	V_{DS}=650 V, V_{GS}=0V,				μA
		T_j = 25°C	-	-	1	
		T_j = 125°C	-	50	-	
Gate leakage current, forward	I_{GSSF}	V_{GS}=20V, V_{DS}=0V	-	-	100	nA
Gate leakage current, reverse	I_{GSSR}	V_{GS}=-20V, V_{DS}=0V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=6A	-			
		T_j = 25°C	-	0.165	0.19	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS}= 100V, V_{GS}= 0V,	-	1470	-	
Output capacitance	C_{oss}	f = 1 MHz	-	59	-	pF
Reverse transfer capacitance	C_{rss}		-	1.2	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 300V, I_D = 10A	-	34	-	
Rise time	t_r	R_G = 25Ω, V_{GS}=10V	-	41	-	ns
Turn-off delay time	$t_{d(off)}$		-	118	-	
Fall time	t_f		-	40	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DD}=480V, I_D=10A,	-	7.2	-	
Gate to drain charge	Q_{gd}	V_{GS}=0 to 10V	-	16	-	nC
Gate charge total	Q_g		-	36	-	
Gate plateau voltage	$V_{plateau}$		-	5.0	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=6A	-	-	1.2	V
Reverse recovery time	t_{rr}	V_R=50V, I_F=10A,	-	290	-	ns
Reverse recovery charge	Q_{rr}	dI_F/dt=100A/μs	-	3.2	-	μC
Peak reverse recovery current	I_{rrm}		-	22	-	A

Notes:

1. Limited by $T_{j\,max}$. Maximum duty cycle D=0.5.

2. Pulse width limited by maximum junction temperature.

3. I_{AS} = 3.8 A, V_{DD} = 50V, R_G = 25Ω, starting T_j = 25°C.

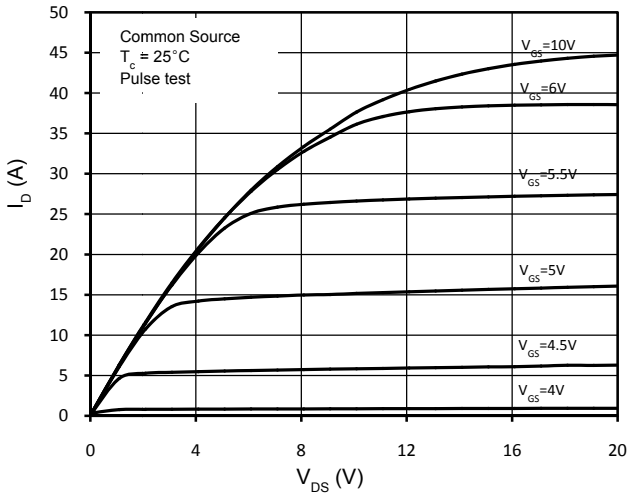


Figure 1.On-Region Characteristics

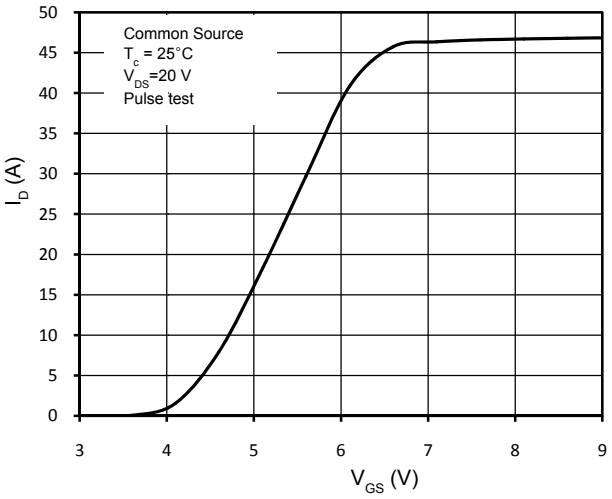


Figure 2. Transfer Characteristics

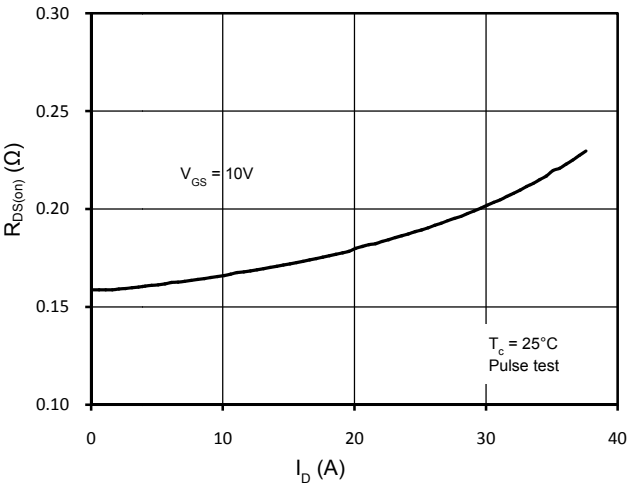


Figure 3. Static Drain-Source On Resistance

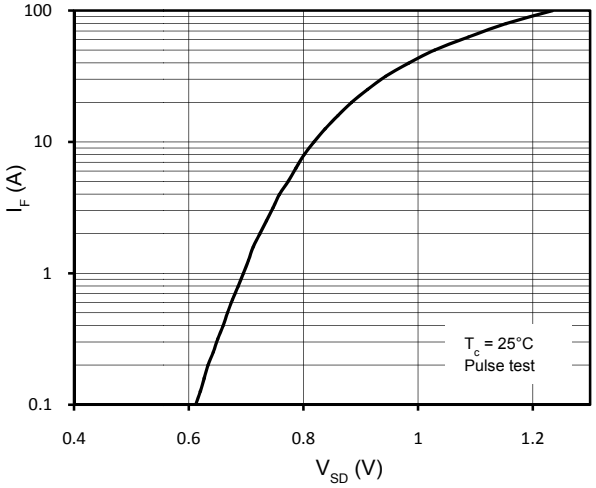


Figure 4. Body- Diode Forward Characteristics

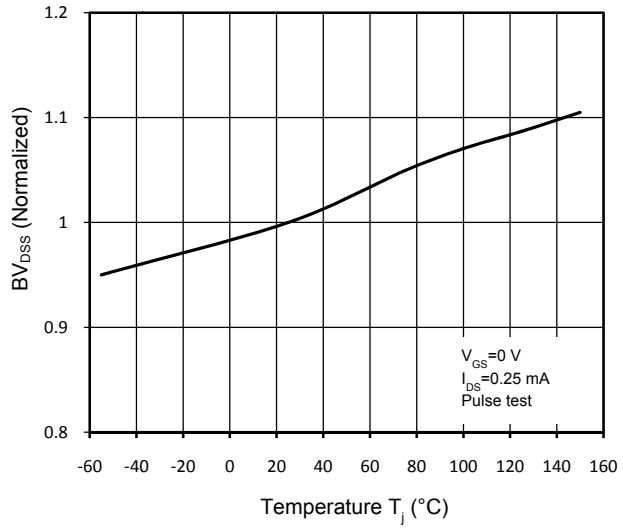


Figure 5. Normalized BV_{DSS} vs. Temperature

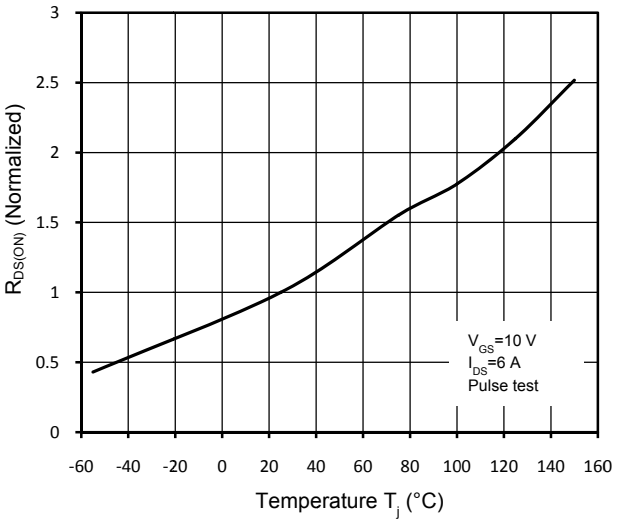


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

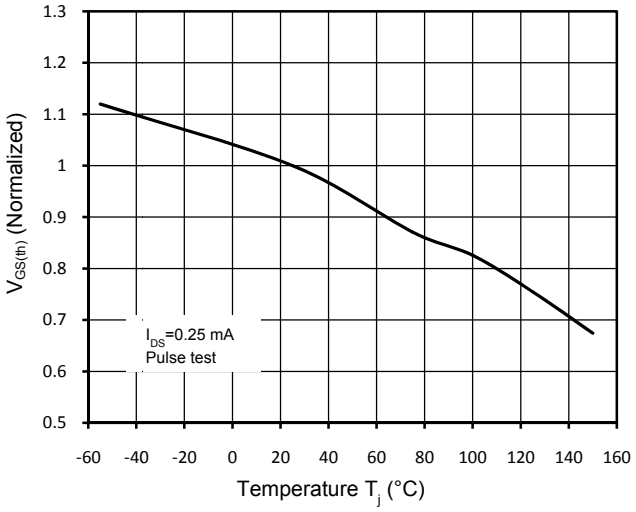


Figure 7. Threshold Voltage vs. Temperature

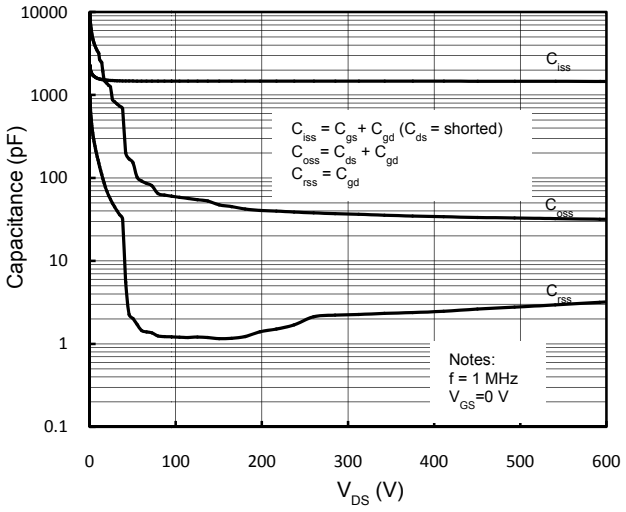


Figure 8. Capacitance Characteristics

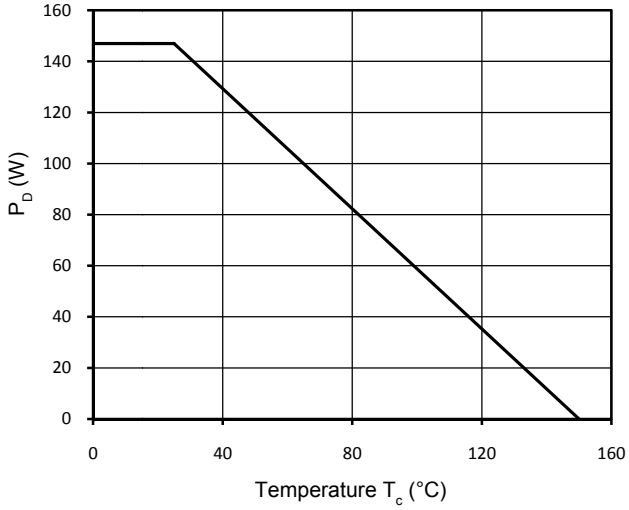


Figure 9. Power Dissipation

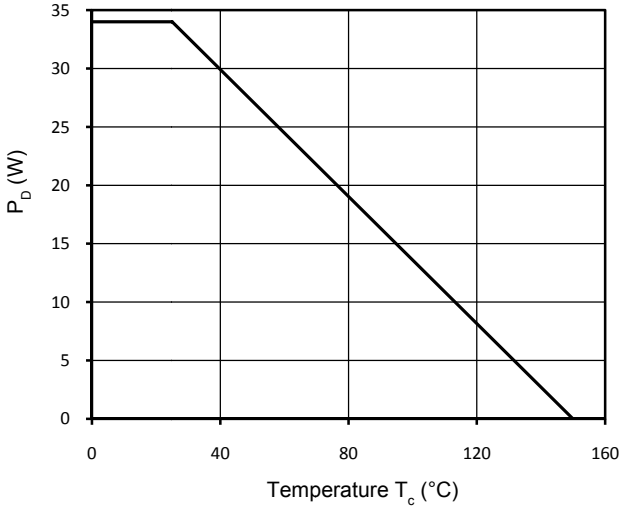


Figure 10. Power Dissipation (TO-220F)

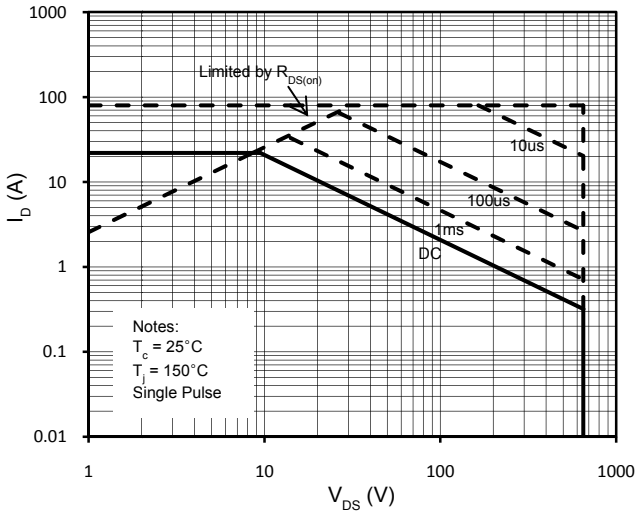


Figure 11. Maximum Safe Operating Area

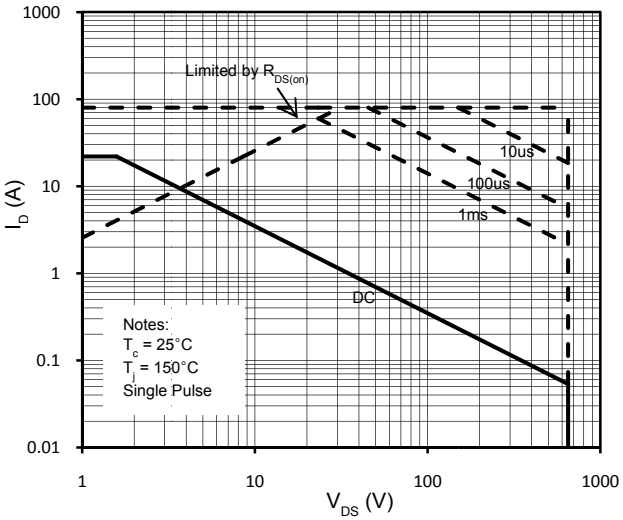


Figure 12. Maximum Safe Operating Area(TO-220F)

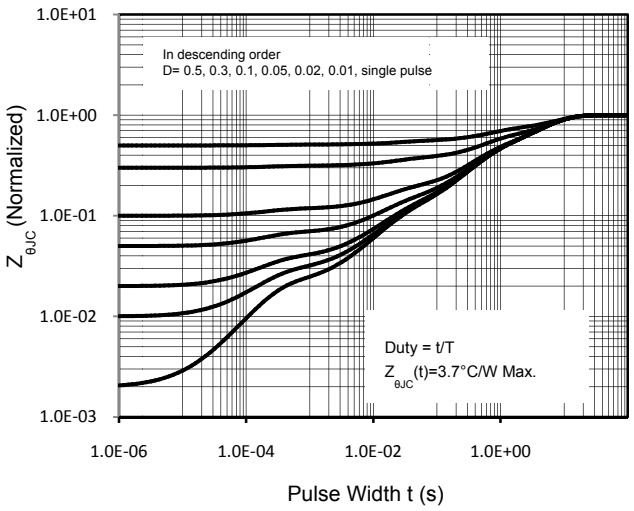


Figure 13. Transient Thermal Response Curve (TO-220F)

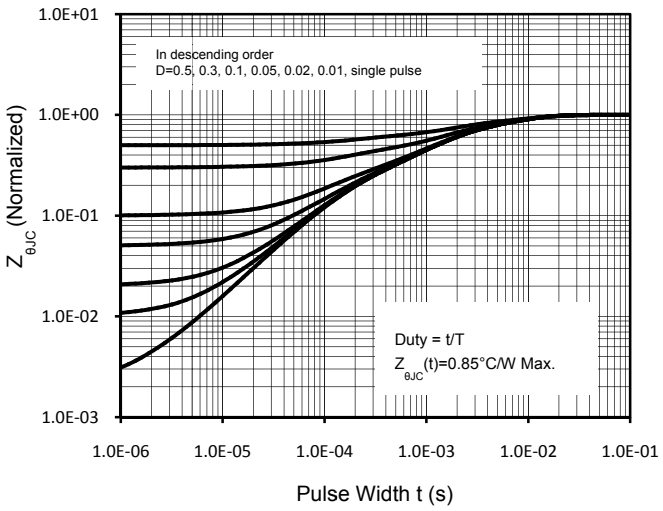


Figure 14. Transient Thermal Response Curve

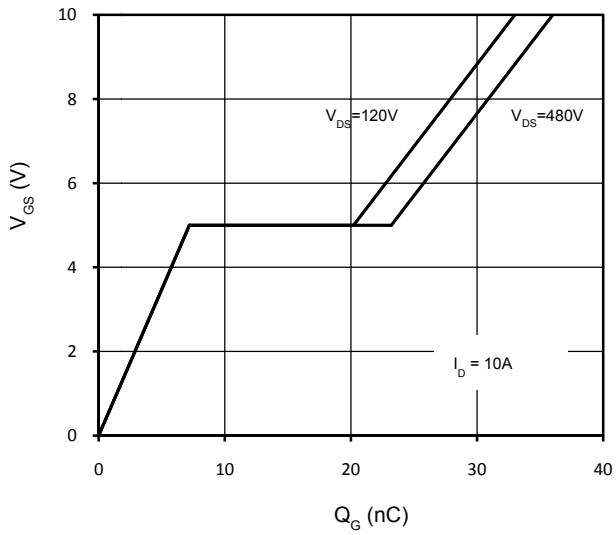
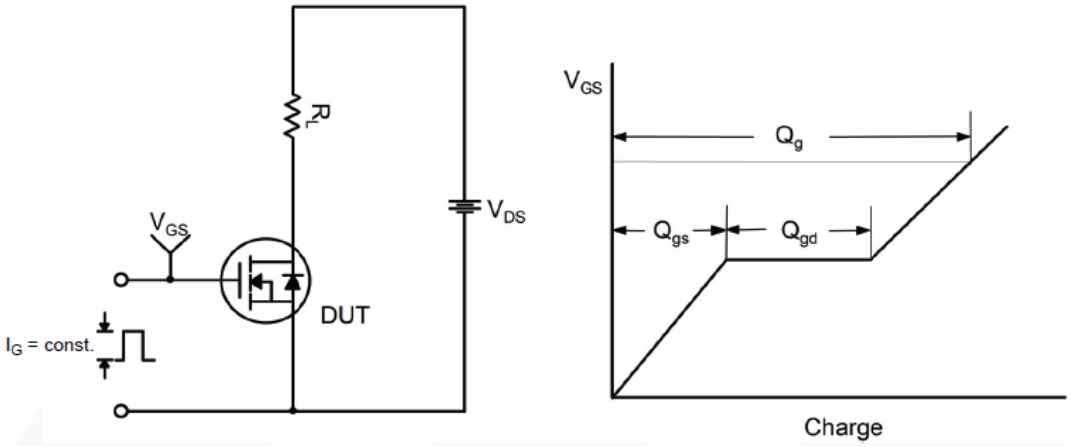
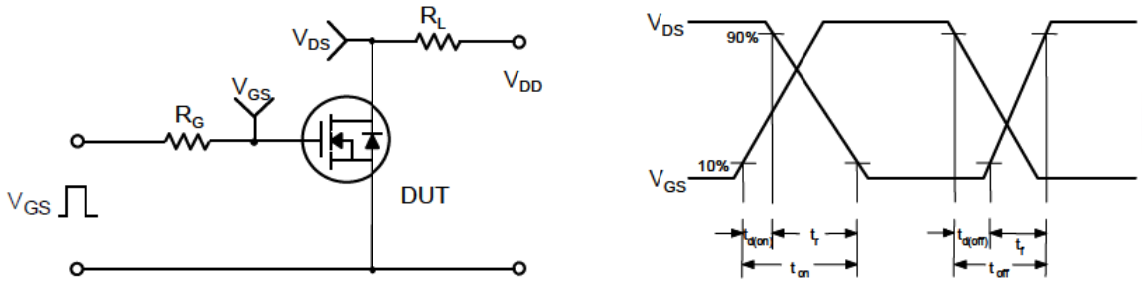


Figure 15. Gate Charge Characteristics

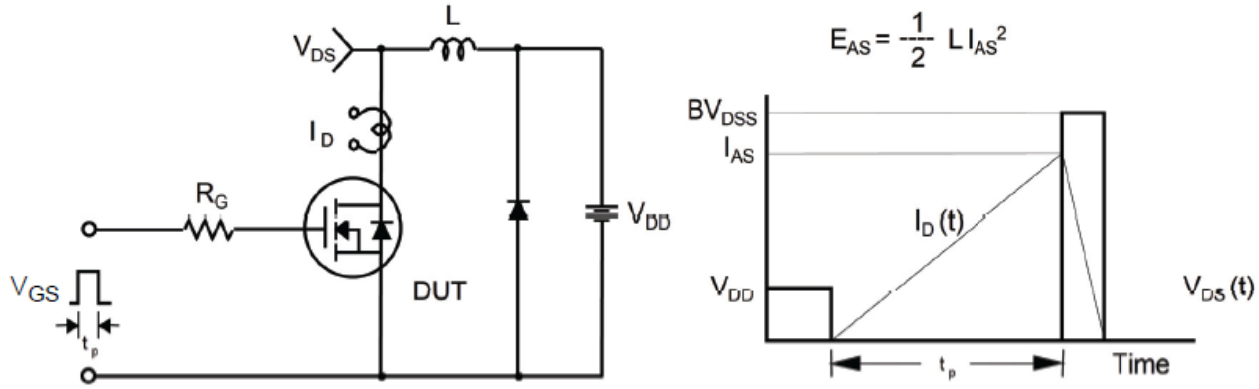
Gate Charge Test Circuit & Waveform



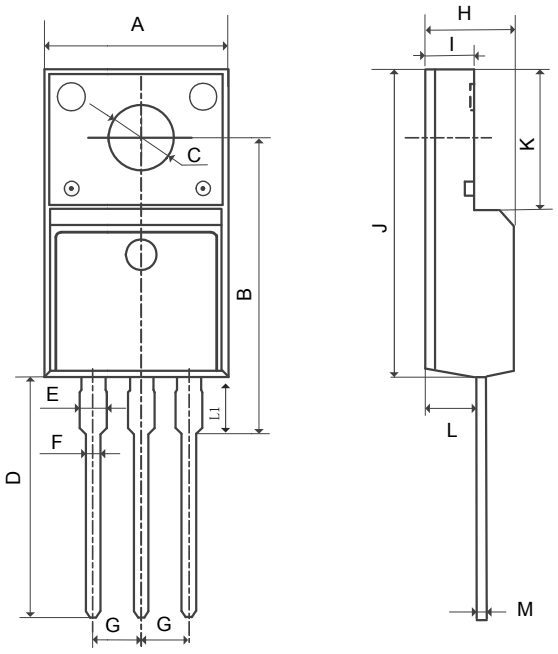
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



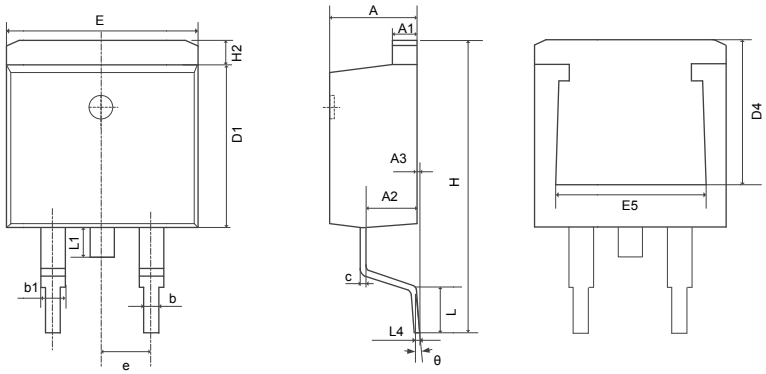
Mechanical Dimensions for TO-220F



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	9.96	10.16	10.36
B	15.10	15.60	16.10
C	3.03	3.20	3.38
D	12.64	12.96	13.28
E	1.18	1.38	1.58
F	0.70	0.81	0.95
G	2.54REF		
H	4.50	4.70	4.90
I	2.34	2.54	2.74
J	15.57	15.87	16.17
K	6.70REF		
L	2.56	2.76	2.96
M	0.40	0.52	0.65
L1	2.85	3.10	3.45

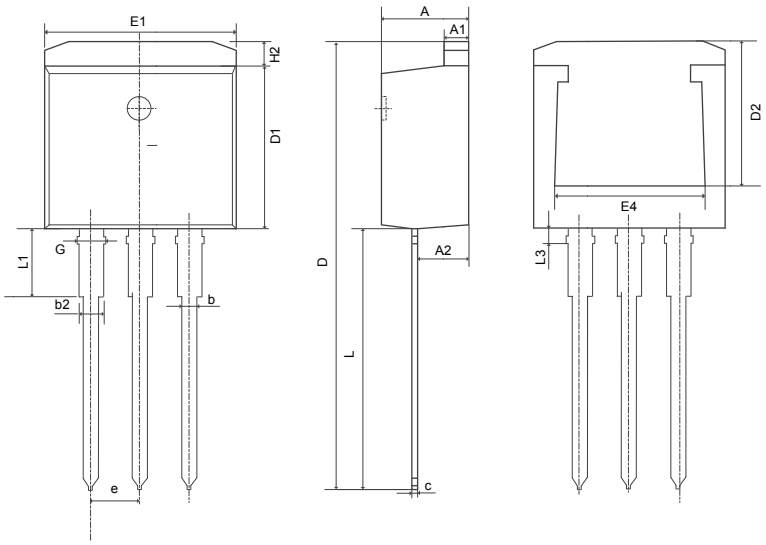
Mechanical Dimensions for TO-263



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	—	—
E	9.86	10.16	10.36
E5	7.06	—	—
e	2.54BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.3	2.60
L1	1.40	1.55	1.70
L4	0.25BSC		
θ	0°	5°	9°

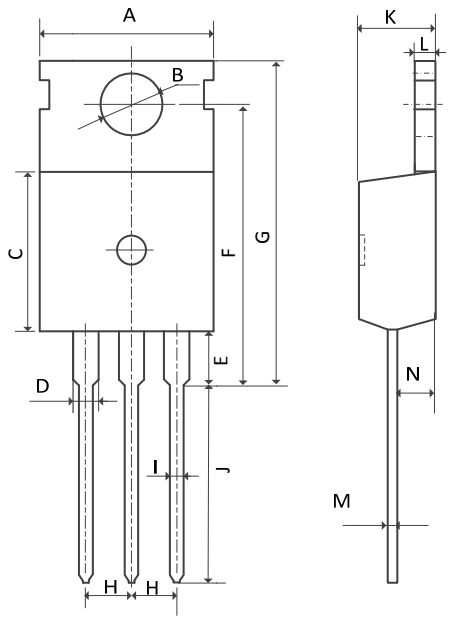
Mechanical Dimensions for TO-262



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
b	0.71	0.81	0.96
b2	1.17	1.27	1.42
c	0.28	0.38	0.53
D	23.20	23.70	24.02
D1	8.50	8.7	8.90
D2	6.00	—	—
E1	9.86	10.16	10.36
E4	7.06	—	—
e	2.54BSC		
G	1.25	1.35	1.50
H2	—	—	1.50
L	13.33	13.73	14.13
L1	3.50	3.75	4.00
L3	1.28	1.43	1.58

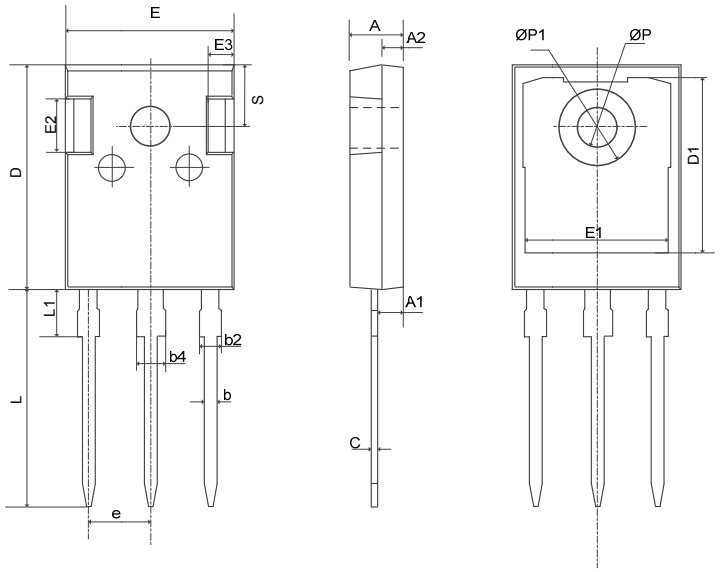
Mechanical Dimensions for TO-220



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	9.70	10.00	10.20
B	3.40	3.60	3.80
C	8.90	9.10	9.40
D	1.17	1.27	1.47
E	2.60	3.10	3.40
F	15.10	15.80	16.70
G	19.55MAX		
H	2.54REF		
I	0.70	0.80	0.95
J	9.35	10.30	11.00
K	4.30	4.57	4.77
L	1.20	1.30	1.45
M	0.40	0.50	0.65
N	2.20	2.40	2.60

Mechanical Dimensions for TO-247



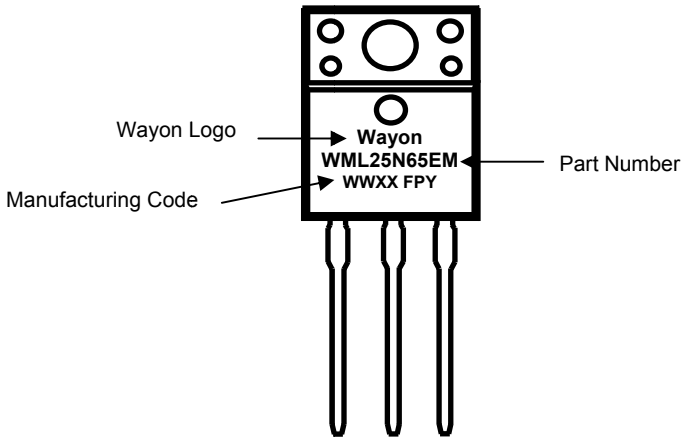
COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.60
E3	2.10	2.50	2.70
e	5.44BSC		
L	19.62	19.92	20.22
L1	—	—	4.30
ØP	3.40	3.60	3.80
ØP1	—	—	7.30
S	6.15BSC		

Ordering Information

Part	Package	Marking	Packing method
WML25N65EM	TO-220F	WML25N65EM	Tube
WMK25N65EM	TO-220	WMK25N65EM	Tube
WMN25N65EM	TO-262	WMN25N65EM	Tube
WMM25N65EM	TO-263	WMM25N65EM	Tape and Reel
WMJ25N65EM	TO-247	WMJ25N65EM	Tube

Marking Information



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